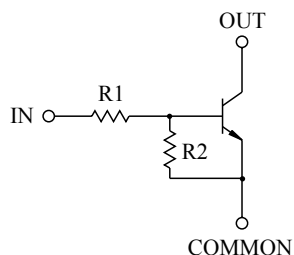


SWITCHING APPLICATION.  
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

### FEATURES

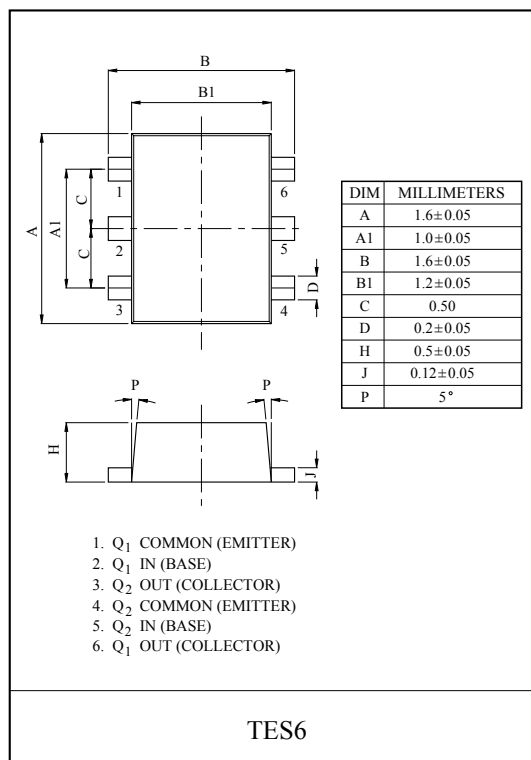
- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.
- High Packing Density.

### EQUIVALENT CIRCUIT

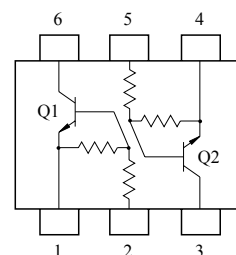


### BIAS RESISTOR VALUES

TYPE NO.	R1(k $\Omega$ )	R2(k $\Omega$ )
KRC857E	10	47
KRC858E	22	47
KRC859E	47	22



### EQUIVALENT CIRCUIT (TOP VIEW)



### MAXIMUM RATING (Ta=25℃)

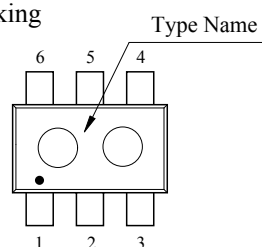
CHARACTERISTIC		SYMBOL	RATING	UNIT
Output Voltage	KRC857E ~ 859E	V <sub>O</sub>	50	V
Input Voltage	KRC857E	V <sub>I</sub>	30, -6	V
	KRC858E		40, -7	
	KRC859E		40, -15	
Output Current	KRC857E ~ 859E	I <sub>O</sub>	100	mA
Power Dissipation		P <sub>D</sub> *	200	mW
Junction Temperature		T <sub>j</sub>	150	℃
Storage Temperature Range		T <sub>stg</sub>	-55 ~ 150	℃

\* Total Rating.

### MARK SPEC

TYPE	KRC857E	KRC858E	KRC859E
MARK	NH	NI	NJ

### Marking



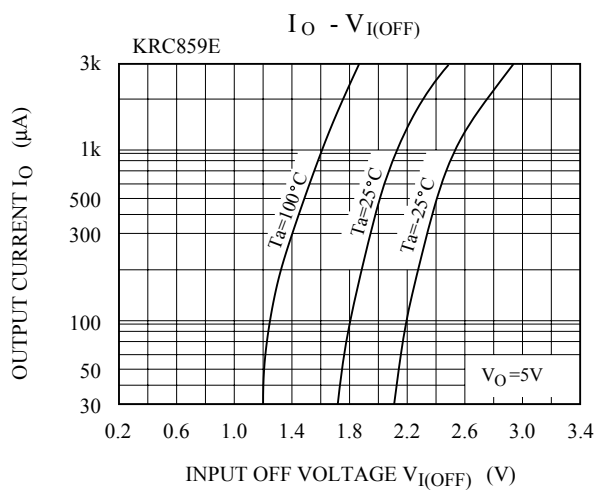
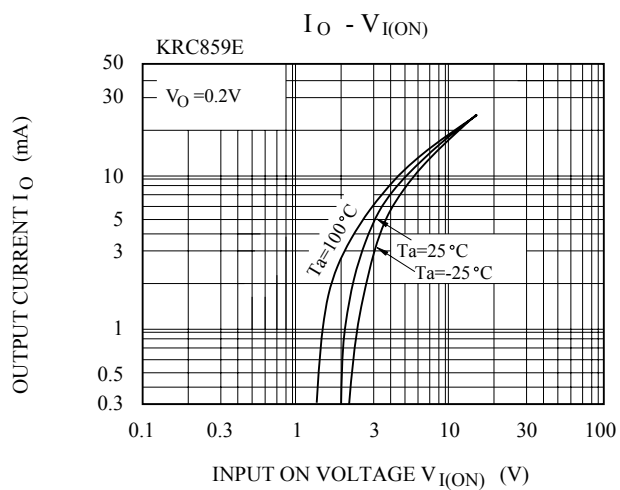
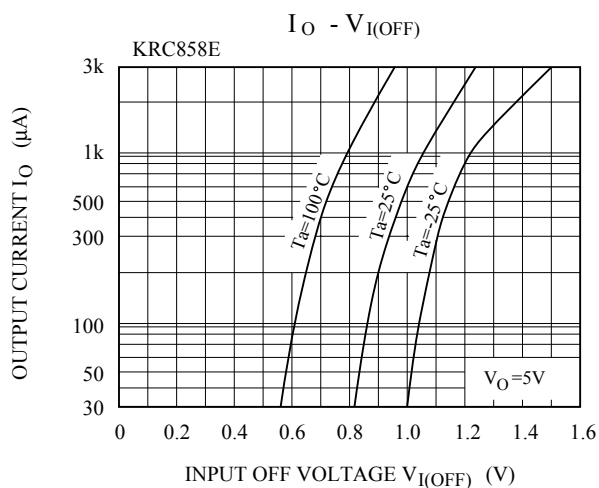
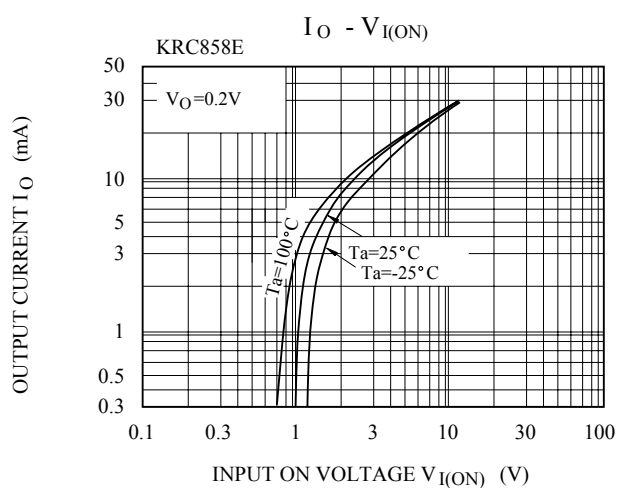
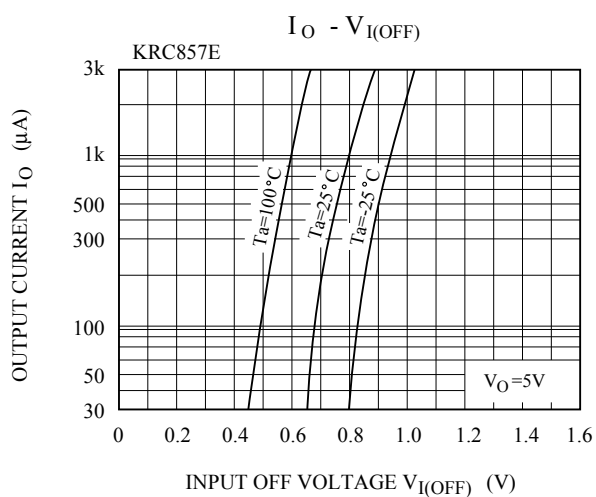
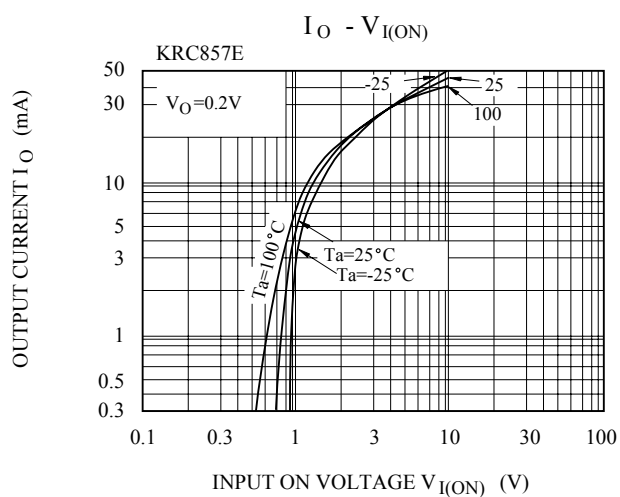
# KRC857E~KRC859E

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC			SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Cut-off Current		KRC857E ~ 859E	I <sub>O(OFF)</sub>	V <sub>O</sub> =50V, V <sub>I</sub> =0	-	-	500	nA
DC Current Gain		KRC857E	G <sub>I</sub>	V <sub>O</sub> =5V, I <sub>O</sub> =10mA	80	150	-	
		KRC858E			80	150	-	
		KRC859E			70	140	-	
Output Voltage		KRC857E ~ 859E	V <sub>O(ON)</sub>	I <sub>O</sub> =10mA, I <sub>I</sub> =0.5mA	-	0.1	0.3	V
Input Voltage (ON)		KRC857E	V <sub>I(ON)</sub>	V <sub>O</sub> =0.2V, I <sub>O</sub> =5mA	-	1.2	1.8	V
		KRC858E			-	1.8	2.6	
		KRC859E			-	3.0	5.8	
Input Votlage (OFF)		KRC857E	V <sub>I(OFF)</sub>	V <sub>O</sub> =5V, I <sub>O</sub> =0.1mA	0.5	0.75	-	V
		KRC858E			0.6	0.88	-	
		KRC859E			1.5	1.82	-	
Transition Frequency		KRC857E ~ 859E	f <sub>I</sub> *	V <sub>O</sub> =10V, I <sub>O</sub> =5mA	-	200	-	MHz
Input Current		KRC857E	I <sub>I</sub>	V <sub>I</sub> =5V	-	-	0.88	mA
		KRC858E			-	-	0.36	
		KRC859E			-	-	0.16	
Switching Time	Rise Time	KRC857E	t <sub>r</sub>	V <sub>O</sub> =5V, V <sub>IN</sub> =5V R <sub>L</sub> =1kΩ	-	0.05	-	μS
		KRC858E			-	0.12	-	
		KRC859E			-	0.26	-	
	Storage Time	KRC857E	t <sub>stg</sub>		-	2.0	-	
		KRC858E			-	2.4	-	
		KRC859E			-	1.5	-	
	Fall Time	KRC857E	t <sub>f</sub>		-	0.36	-	
		KRC858E			-	0.4	-	
		KRC859E			-	0.41	-	

Note : \* Characteristic of Transistor Only.

# KRC857E~KRC859E



# KRC857E~KRC859E

